



2SC2060 TRANSISTOR (NPN)

FEATURE

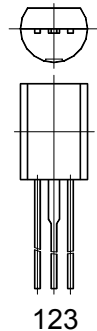
- Power dissipation P_{CM} : 0.75 W ($T_{amb}=25^{\circ}C$)
- Low saturation voltage ($V_{CE(sat)}=0.15V$ at 500mA)
- Complementary pair with 2SA934

MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-base voltage	40	V
V_{CEO}	Collector-Emitter Voltage	32	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1	A
P_C	Collector Power Dissipation	750	mW
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$

TO-92L

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C=100\mu A, I_E=0$	40		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C=1mA, I_B=0$	32		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E=100\mu A, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=20V, I_E=0$		0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$		0.1	μA
DC current gain	h_{FE}	$V_{CE}=3V, I_C=100mA$	80	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$		0.4	V
Transition frequency	f_T	$V_{CE}=5V, I_E=-50mA$	50		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		30	pF